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Rue	AB	3,98	2,268	09/76	Anthony et al.		257	45	03/14	11978	
Sevie	AC	5,61	8,752	04/97	Gaul		438	624	06/03	5/1995	
icer	AD	4,39	4,712	07/83	Anthony		361	779	03/18	1981	
Renz	AE	5,76	7,001	06/98	Bertagnolli et al.		434	455	05/02	1994	
Jul	AF	5,80	7,783	09/98	Gaul et al.		438	404	10/07	1996	
DUR	AG	4,97	7,439	12/90	Esquivel et al.		257	621	०५/०३	1989	
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Jun	AK	5,71	7,247	02/98	Koh et al.	· · · · · · · · · · · · · · · · · · ·	257	686	11/5/	1996	
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Sur	/ AC	5,646,067	07/97	Gaul		438	458	06/05/	1995		
Dur	AD	5,640,049	06/97	Rostoker et al.		857	758	11/30/	1995		
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Deen	AI	5,317,197	05/94	Roberts		057	407	<u>બ્</u> યાંગા	1993		
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Dur	AB	5,750	0,436	05/98	Yamaga et al.		438	558	01/07/1995		
Due	AC	4,419	9,150	12/83	Sociof		438	337	09/16/1982		
Tun	AD	5,424	1,245	06/95	Gurtler et al.		438	107	01/04/1994		
Eun	AE	5,841	1,197	11/98	Adamic, Jr.		957	777	09/05/1996		
Peur	AF	5,990),562	11/99	Vallett		257	774	02/25/1997		
Dur	AG	6,037	1,244	03/00	Gardner et al.		438	586	03/19/1997		
Tur	AH	5,933	3,758	08/99	Jain		438	687	05/12/1997		
Pur	Ai	5,539	7,227	07./96	Nakano		257	274	08/00/1995		
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Sheet 5 of 6 SERIAL NO. U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE ATTY, DOCKET NO. MI22-1738 Form PTO-1449 LIST OF ART CITED BY APPLICANT (Use several sheets if necessary) Kie Y. Ahn FILING DATE GROUP U.S. PATENT DOCUMENTS Date Class Subclass Filing Date *Examiner Document Name Initial Number If Appropriate 438 p28 Dennison et al. AA 5,651,855 07/97 ΑB 4,440,973 04/84 Hawkins 4,776,087 10/88 Cronin et al. 29 &ે ૪ 5,148,260 257 AD 09/92 Inoue et al. ΑE 5,528,080 06/96 Goldstein Q57 5,539,256 07/96 Mikagi AG 5,608,237 03/97 Aizawa et al. 257 132 438 AH 5,817,572 10/98 Chiang et al. ΑI 5,827,775 10/98 Miles et al. 438 622 AJ 5,596,230 01/97 Hong 257 438 700 ΑK 5,858,877 01/99 Dennison et al. FOREIGN PATENT DOCUMENTS Date Class Subclass Translation Document Country Number Yes No ΑL AM AN AO OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

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